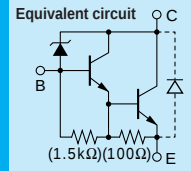


Built-in Avalanche Diode for Surge Absorbing Darlington

2SD2141



Silicon NPN Triple Diffused Planar Transistor

Application : Ignitor, Driver for Solenoid and Motor, and General Purpose

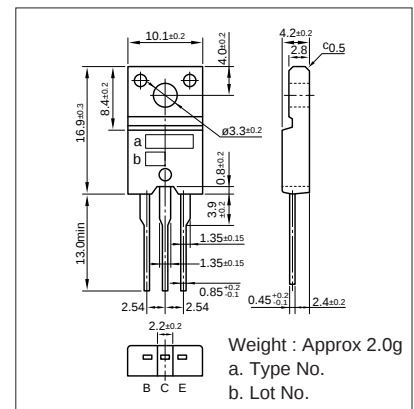
Absolute maximum ratings (Ta=25°C)

Symbol	2SD2141	Unit
VCBO	380±50	V
VCEO	380±50	V
VEBO	6	V
IC	6(Pulse10)	A
IB	1	A
PC	35(Tc=25°C)	W
Tj	150	°C
Tstg	-55 to +150	°C

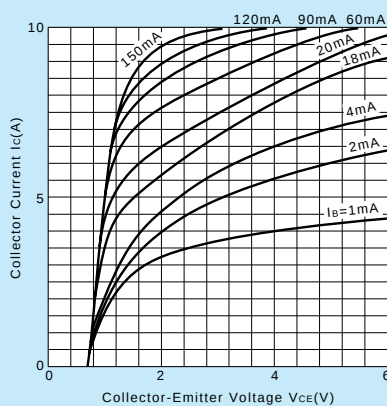
Electrical Characteristics (Ta=25°C)

Symbol	Conditions	2SD2141	Unit
ICBO	VCB=330V	10max	μA
IEBO	VEB=6V	20max	mA
V(BR)CEO	IC=25mA	330 to 430	V
hFE	VCE=2V, IC=3A	1500min	
VCE(sat)	IC=4A, IB=20mA	1.5max	V
fr	VCE=12V, IE=-0.5A	20typ	MHz
COB	VCB=10V, f=1MHz	95typ	pF

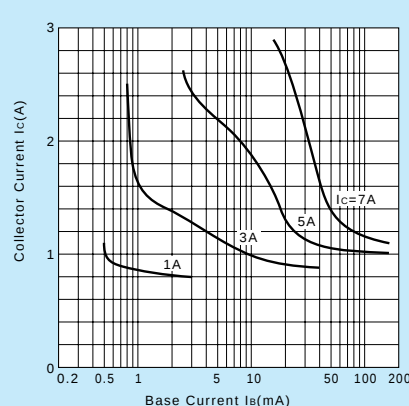
External Dimensions FM20(TO220F)



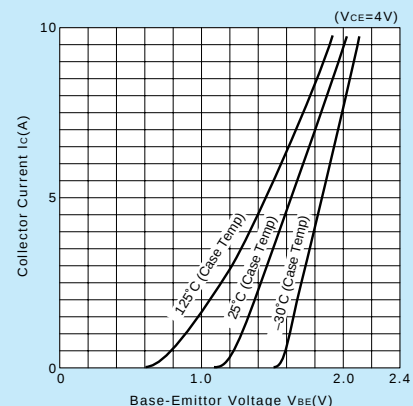
IC-VCE Characteristics (Typical)



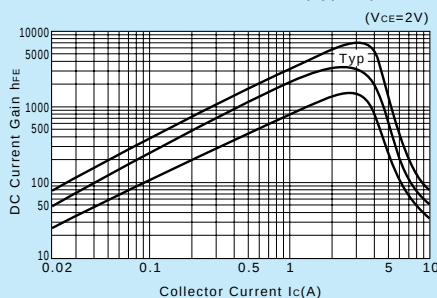
VCE(sat)-IB Characteristics (Typical)



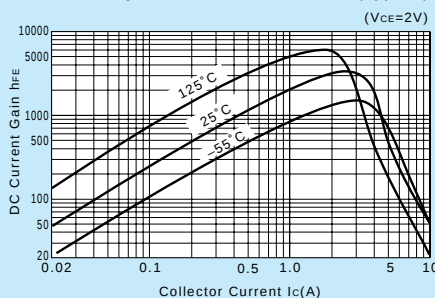
IC-VBE Temperature Characteristics (Typical)



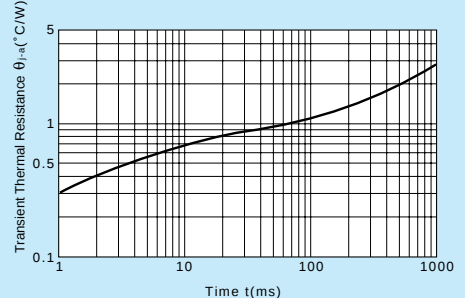
hFE-IC Characteristics (Typical)



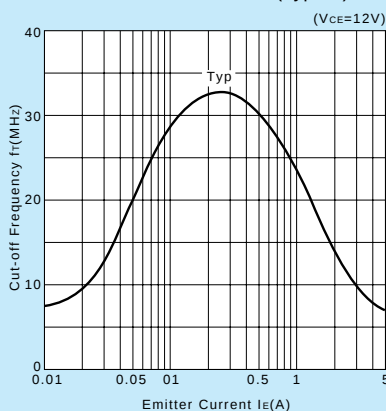
hFE-IC Temperature Characteristics (Typical)



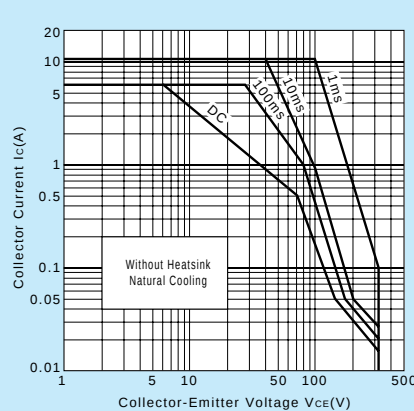
θj-a-t Characteristics



fT-IE Characteristics (Typical)



Safe Operating Area (Single Pulse)



PC-Ta Derating

